ABSTRACT

METHODS OF FORMING SEMICONDUCTOR DEVICES
USING EMBEDDED L-SHAPE SPACERS

A method of forming a semiconductor device that embeds an L-shaped spacer is provided. The method includes defining an L-shaped spacer (16) on each side of a gate region (14) of a substrate (12) and embedding the L-shaped spacers (16) in an oxide layer (28) so that the oxide layer (28) extends over a portion of the substrate a predetermined distance from a lateral edge of the L-shaped spacer (16). In one embodiment, the method further includes the step of removing oxide layers to expose the L-shape spacers.

Fig. 2.

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